

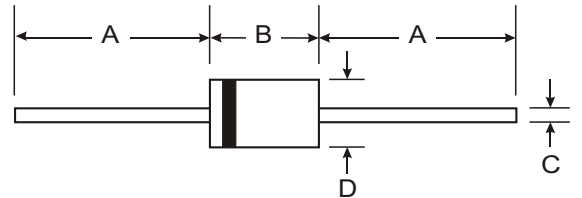
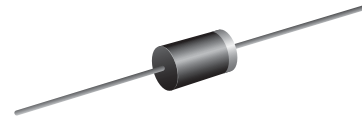
VOLTAGE RANGE: 400 - 1000V
CURRENT: 1.0 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: D O - 4 1 Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



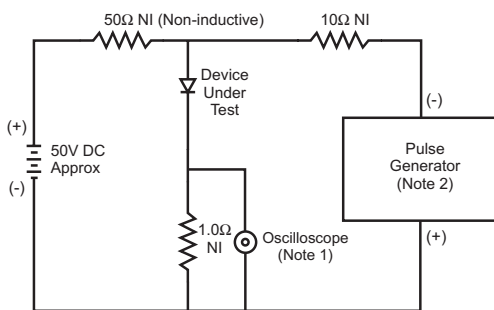
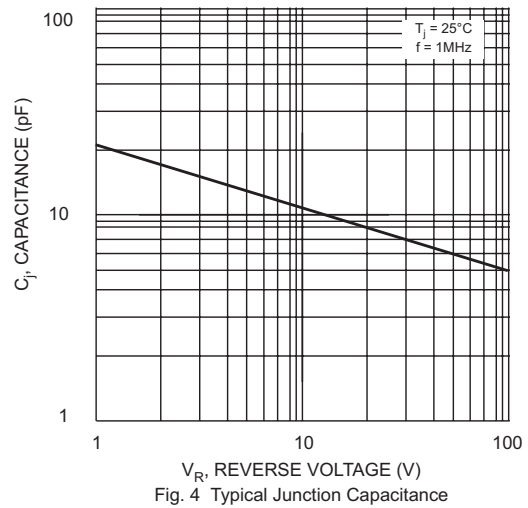
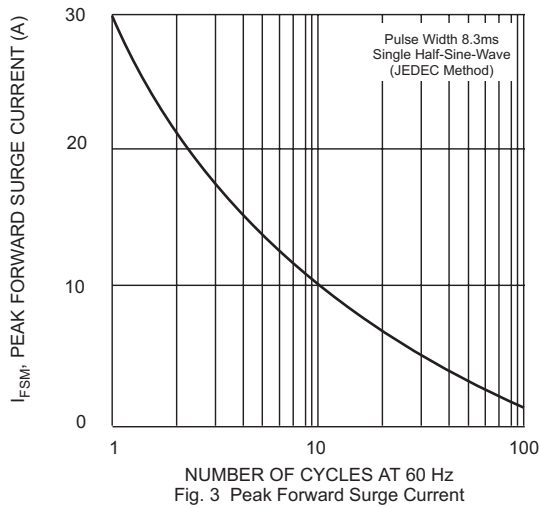
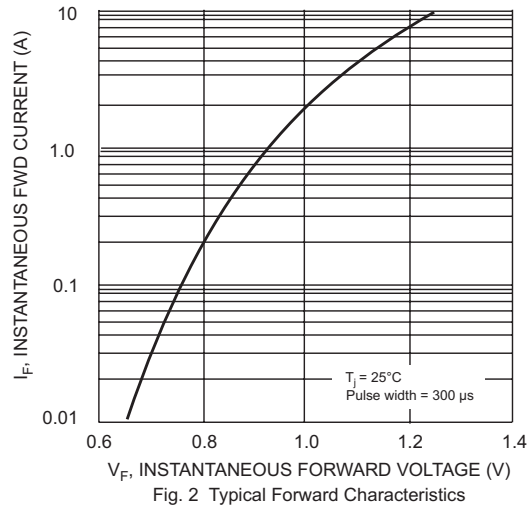
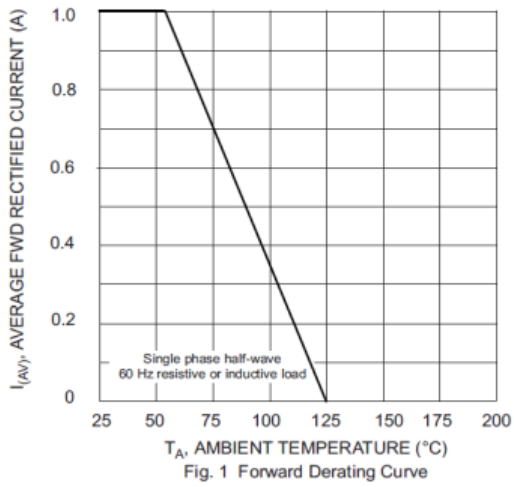
DO-41		
Dim	Min	Max
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	BA157	BA158	BA159	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{VRWM} V _R	400	600	1000	V
RMS Reverse Voltage	V _{R(RMS)}	280	420	700	V
Average Rectified Output Current (Note 1) @T_A = 55°C	I _O	1.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30			A
Forward Voltage @I_F = 1.0A	V _{FM}	1.2			V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I _{RM}	5.0 100			μA
Reverse Recovery Time (Note 2)	t _{rr}	150	250	500	nS
Typical Junction Capacitance (Note 3)	C _j	15			pF
Operating Temperature Range	T _j	-65 to +125			°C
Storage Temperature Range	T _{STG}	-65 to +150			°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case
 2. Measured with I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A. See figure 5.
 3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.



- Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0M Ω , 22pF.
 2. Rise Time = 10ns max. Input Impedance = 50 Ω .

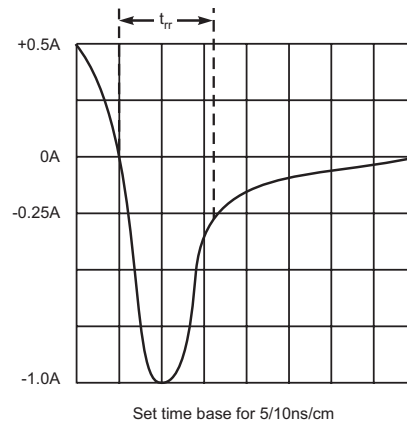


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit